

isc Silicon NPN Power Transistor

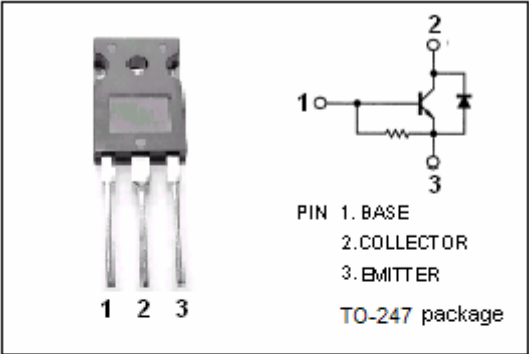
BU2725DW

DESCRIPTION

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

APPLICATIONS

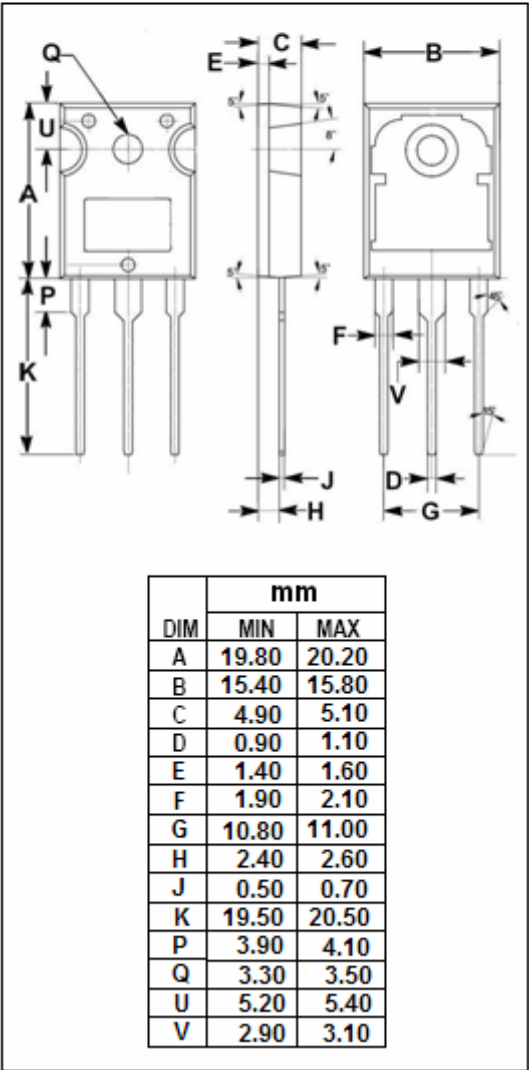
- Designed for use in horizontal deflection circuits of color TV receivers.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage($V_{BE}=0$)	1700	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current- Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current- Continuous	12	A
I_{BM}	Base Current-Peak	20	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	125	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.8	$^{\circ}\text{C/W}$



ISC Silicon NPN Power Transistor**BU2725DW****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 600mA; I _C = 0	7.5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 7A; I _B = 1.75A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 7A; I _B = 1.75A			0.95	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1700V ; V _{BE} = 0 V _{CE} = 1700V ; V _{BE} = 0; T _C =125°C			1.0 2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7.5V ; I _C = 0		110		mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 5V		19		
h _{FE-2}	DC Current Gain	I _C = 7A ; V _{CE} = 1V	3.8		7.8	
V _{ECF}	C-E Diode Forward Voltage	I _F = 7A			2.2	V